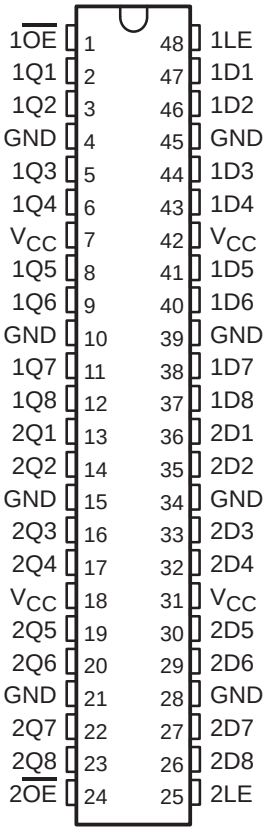
- **State-of-the-Art Advanced BiCMOS Technology (ABT) *Widebus*™ Design for 2.5-V and 3.3-V Operation and Low Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 2.3-V to 3.6-V V_{CC})**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **High Drive (–24/24 mA at 2.5-V and –32/64 mA at 3.3-V V_{CC})**
- **Power Off Disables Outputs, Permitting Live Insertion**
- **High-Impedance State During Power Up and Power Down Prevents Driver Conflict**
- **Uses Bus Hold on Data Inputs in Place of External Pullup/Pulldown Resistors to Prevent the Bus From Floating**
- **Auto3-State Eliminates Bus Current Loading When Output Exceeds V_{CC} + 0.5 V**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model; and Exceeds 1000 V Using Charged-Device Model, Robotic Method**
- **Flow-Through Architecture Facilitates Printed Circuit Board Layout**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Package Options Include Plastic Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), Thin Very Small-Outline (DGV) Packages, and 380-mil Fine-Pitch Ceramic Flat (WD) Package**

SN54ALVTH16373 . . . WD PACKAGE
SN74ALVTH16373 . . . DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

The ’ALVTH16373 devices are 16-bit transparent D-type latches with 3-state outputs designed for 2.5-V or 3.3-V V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

These devices can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

description (continued)

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

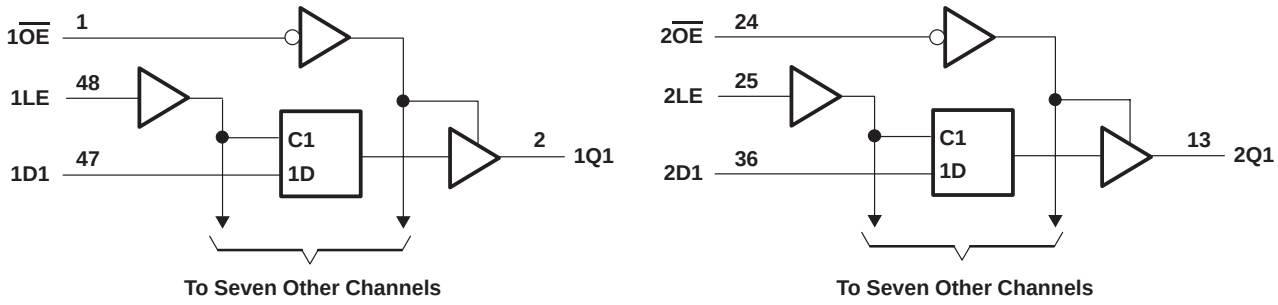
When V_{CC} is between 0 and 1.2 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.2 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54ALVTH16373 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ALVTH16373 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Output current in the low state, I_O: SN54ALVTH16373 . . . . . 96 mA
SN74ALVTH16373 . . . . . 128 mA
Output current in the high state, I_O: SN54ALVTH16373 . . . . . –48 mA
SN74ALVTH16373 . . . . . –64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 2): DGG package . . . . . 89°C/W
DGV package . . . . . 93°C/W
DL package . . . . . 94°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions, V_{CC} = 2.5 V ± 0.2 V (see Note 3)

			SN54ALVTH16373			SN74ALVTH16373			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{CC}	Supply voltage		2.3		2.7	2.3		2.7	V
V_{IH}	High-level input voltage		1.7			1.7			V
V_{IL}	Low-level input voltage				0.7			0.7	V
V_I	Input voltage		0		5.5	0		5.5	V
I_{OH}	High-level output current				–6			–8	mA
I_{OL}	Low-level output current				6			8	mA
	Low-level output current; current duty cycle ≤ 50%; f ≥ 1 kHz				18			24	
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled			10			10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200			200			µs/V
T_A	Operating free-air temperature		–55		125	–40		85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

recommended operating conditions, V_{CC} = 3.3 V ± 0.3 V (see Note 3)

			SN54ALVTH16373			SN74ALVTH16373			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{CC}	Supply voltage		3		3.6	3		3.6	V
V_{IH}	High-level input voltage		2			2			V
V_{IL}	Low-level input voltage				0.8			0.8	V
V_I	Input voltage		0	V_{CC}	5.5	0	V_{CC}	5.5	V
I_{OH}	High-level output current				–24			–32	mA
I_{OL}	Low-level output current				24			32	mA
	Low-level output current; current duty cycle ≤ 50%; f ≥ 1 kHz				48			64	
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled			10			10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200			200			µs/V
T_A	Operating free-air temperature		–55		125	–40		85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54ALVTH16373			SN74ALVTH16373			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.3 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.3 V to 2.7 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.3 V	I_{OH} = –6 mA	1.8						
			I_{OH} = –8 mA				1.8			
V_{OL}		V_{CC} = 2.3 V to 2.7 V,	I_{OL} = 100 µA			0.2			0.2	V
		V_{CC} = 2.3 V	I_{OL} = 6 mA			0.4				
			I_{OL} = 8 mA						0.4	
			I_{OL} = 18 mA			0.5				
			I_{OL} = 24 mA						0.5	
I_I	Control inputs	V_{CC} = 2.7 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 2.7 V,	V_I = 5.5 V			10			10	
	Data inputs	V_{CC} = 2.7 V	V_I = 5.5 V			10			10	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
I_{BHL}‡		V_{CC} = 2.3 V,	V_I = 0.7 V		115			115		µA
I_{BHH}§		V_{CC} = 2.3 V,	V_I = 1.7 V		–10			–10		µA
I_{BHLO}¶		V_{CC} = 2.7 V,	V_I = 0 to V_{CC}	300			300			µA
I_{BHHO}#		V_{CC} = 2.7 V,	V_I = 0 to V_{CC}	–300			–300			µA
I_{EX}‖		V_{CC} = 2.3 V,	V_O = 5.5 V			125			125	µA
$I_{OZ(PU/PD)}$☆		V_{CC} ≤ 1.2 V, V_O = 0.5 V to V_{CC}, V_I = GND or V_{CC}, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZH}		V_{CC} = 2.7 V	V_O = 2.3 V, V_I = 0.7 V or 1.7 V			5			5	µA
I_{OZL}		V_{CC} = 2.7 V	V_O = 0.5 V, V_I = 0.7 V or 1.7 V			–5			–5	µA
I_{CC}		V_{CC} = 2.7 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.04	0.1		0.04	0.1	mA
			Outputs low		2.3	4.5		2.3	4.5	
			Outputs disabled		0.04	0.1		0.04	0.1	
C_i		V_{CC} = 2.5 V,	V_I = 2.5 V or 0		3.5			3.5		pF
C_o		V_{CC} = 2.5 V,	V_O = 2.5 V or 0		6			6		pF

† All typical values are at V_{CC} = 2.5 V, T_A = 25°C.
‡ The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.
§ The bus-hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH} min.
¶ An external driver must source at least I_{BHLO} to switch this node from low to high.
# An external driver must sink at least I_{BHHO} to switch this node from high to low.
‖ Current into an output in the high state when V_O > V_{CC}
☆ High-impedance state during power up or power down

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54ALVTH16373			SN74ALVTH16373			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 3 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 3 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 3 V to 3.6 V,	I_{OL} = 100 µA			0.2			0.2	V
		V_{CC} = 3 V	I_{OL} = 16 mA						0.4	
			I_{OL} = 24 mA			0.5				
			I_{OL} = 32 mA						0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	Data inputs	V_{CC} = 3.6 V	V_I = 5.5 V			10			10	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
I_{BHL}‡		V_{CC} = 3 V,	V_I = 0.8 V	75			75			µA
I_{BHH}§		V_{CC} = 3 V,	V_I = 2 V	–75			–75			µA
I_{BHLO}¶		V_{CC} = 3.6 V,	V_I = 0 to V_{CC}	500			500			µA
I_{BHHO}#		V_{CC} = 3.6 V,	V_I = 0 to V_{CC}	–500			–500			µA
I_{EX}‖		V_{CC} = 3 V,	V_O = 5.5 V			125			125	µA
$I_{OZ(PU/PD)}$☆		V_{CC} ≤ 1.2 V, V_O = 0.5 V to V_{CC}, V_I = GND or V_{CC}, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZH}		V_{CC} = 3.6 V	V_O = 3 V, V_I = 0.8 V or 2 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V	V_O = 0.5 V, V_I = 0.8 V or 2 V			–5			–5	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.07	0.1		0.07	0.1	mA
			Outputs low		3.2	5.5		3.2	5	
			Outputs disabled		0.07	0.1		0.07	0.1	
ΔI_{CC}□		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.4			0.4	mA
C_i		V_{CC} = 3.3 V,	V_I = 3.3 V or 0		3.5			3.5		pF
C_o		V_{CC} = 3.3 V,	V_O = 3.3 V or 0		6			6		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.
§ The bus-hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH} min.
¶ An external driver must source at least I_{BHLO} to switch this node from low to high.
# An external driver must sink at least I_{BHHO} to switch this node from high to low.
‖ Current into an output in the high state when V_O > V_{CC}
☆ High-impedance state during power up or power down
□ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

			SN54ALVTH16373		SN74ALVTH16373		UNIT
			MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high		1.5		1.5		ns
t_{su}	Setup time, data before LE↓	Data high	1.1		1		ns
		Data low	1.6		1.5		
t_h	Hold time, data after LE↓	Data high	1		0.9		ns
		Data low	1.6		1.5		

timing requirements over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 2)

			SN54ALVTH16373		SN74ALVTH16373		UNIT
			MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high		1.5		1.5		ns
t_{su}	Setup time, data before LE↓	Data high	1.5		1.4		ns
		Data low	1		0.9		
t_h	Hold time, data after LE↓	Data high	1		0.9		ns
		Data low	1.5		1.4		

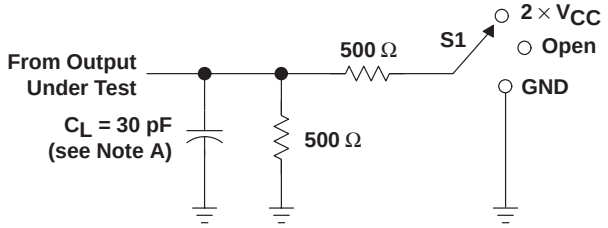
switching characteristics over recommended operating free-air temperature range, C_L = 30 pF, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ALVTH16373		SN74ALVTH16373		UNIT
			MIN	MAX	MIN	MAX	
t_{PLH}	D	Q	1	3.4	1	3.3	ns
t_{PHL}			1	4.3	1	4.2	
t_{PLH}	LE	Q	1.4	3.9	1.5	3.8	ns
t_{PHL}			1.4	4.6	1.5	4.5	
t_{PZH}	$\overline{OE}$	Q	1.7	4.4	1.8	4.3	ns
t_{PZL}			1.4	4.1	1.5	4	
t_{PHZ}	OE	Q	1.4	4.7	1.5	4.6	ns
t_{PLZ}			1	3.7	1	3.6	

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 2)

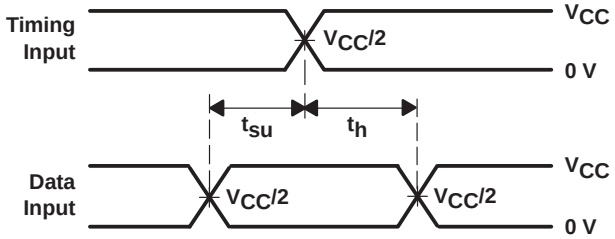
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ALVTH16373		SN74ALVTH16373		UNIT
			MIN	MAX	MIN	MAX	
t_{PLH}	D	Q	1	3.2	1	3.1	ns
t_{PHL}			1	3.4	1	3.3	
t_{PLH}	LE	Q	1	3.4	1	3.3	ns
t_{PHL}			1	3.6	1	3.5	
t_{PZH}	$\overline{OE}$	Q	1.3	4.1	1.4	4	ns
t_{PZL}			1	3.5	1	3.4	
t_{PHZ}	$\overline{OE}$	Q	1.4	5	1.5	4.9	ns
t_{PLZ}			1.4	4.6	1.5	4.5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

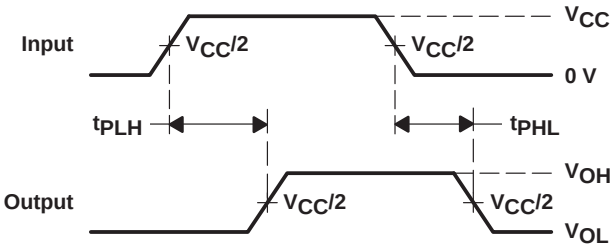


LOAD CIRCUIT

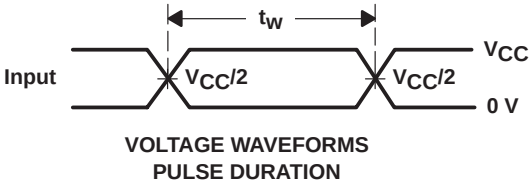
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



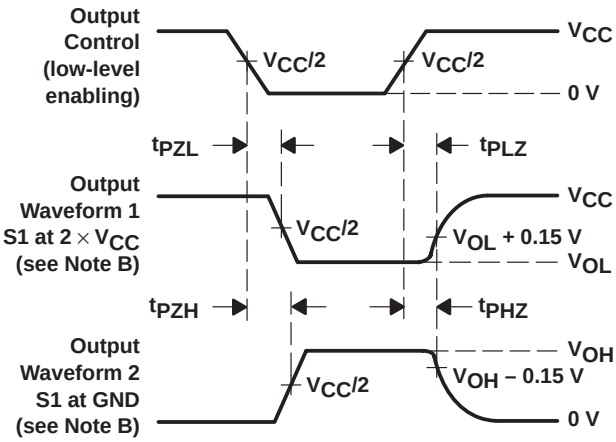
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

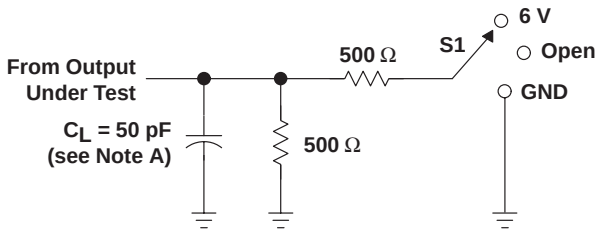


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.

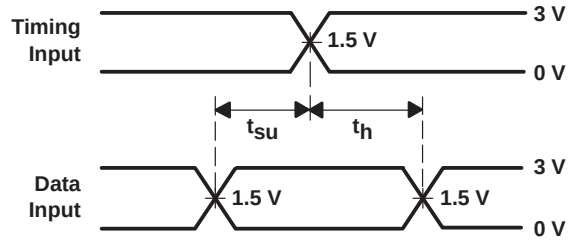
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 3.3 V ± 0.3 V

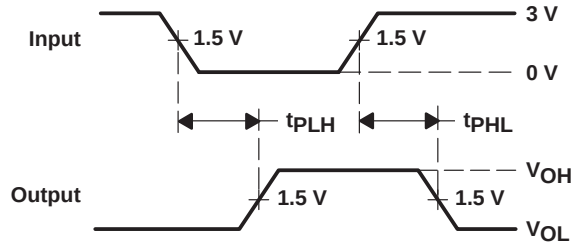


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

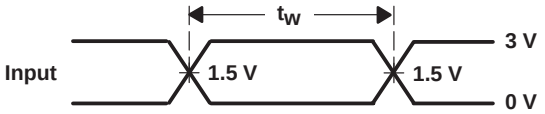
LOAD CIRCUIT



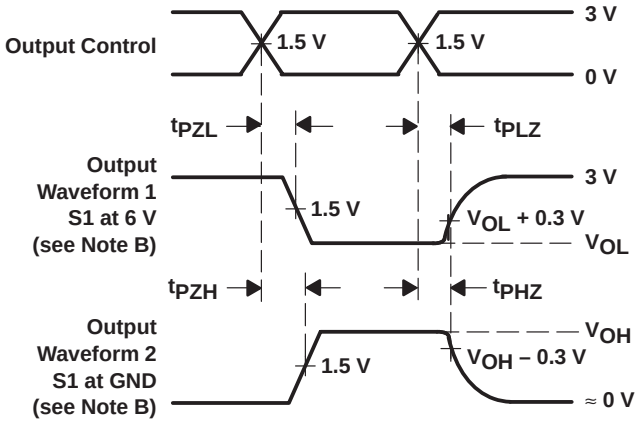
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform22 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

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